



PATENT
Attorney Docket No.: SAM-0274

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Min-su Kim, et al.

Examiner: Hu, S.

Serial No.: 09/994,146

Group Art Unit: 2811

Filing Date: November 26, 2001

Title: SEMICONDUCTOR DEVICE HAVING SILICON-ON-INSULATOR
STRUCTURE AND METHOD OF FABRICATING THE SAME

8/13
1.874070
9-27

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

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9/16/02

Date

Lisa Sanders

Lisa Sanders

BOX NON-FEE AMENDMENT

Assistant Commissioner for Patents

Washington, D.C. 20231

AMENDMENT A

Sir:

This is in response to the Office Action mailed on June 17, 2002.

Please amend the application as follows:

In the Claims

Sub D27

1. (Amended) A semiconductor device having a silicon-on-insulator (SOI) structure, comprising:
an insulating layer;
an insular silicon region having first conductive impurity ions formed on the insulating layer;
a source region having second conductive impurity ions formed at an end of the insular silicon region;

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Cont.

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